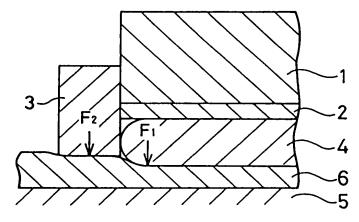


F1G.1

2/8

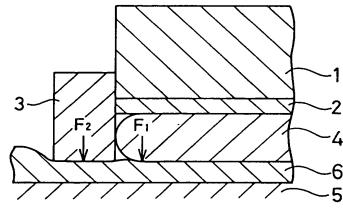
F / G. 2 A

 $\mathsf{F}\iota > \mathsf{F}_2$



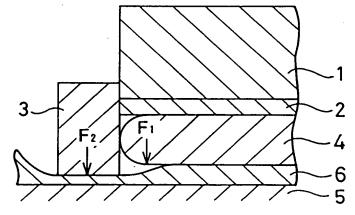
 $F_1 = F_2$

F / G. 2B



 $F_1 < F_2$

F 1 G. 2 C



zezo. Estroso

APPROVED

εY

RAFTSHAH

O.G. FIG.

CLASS SUBCLASS

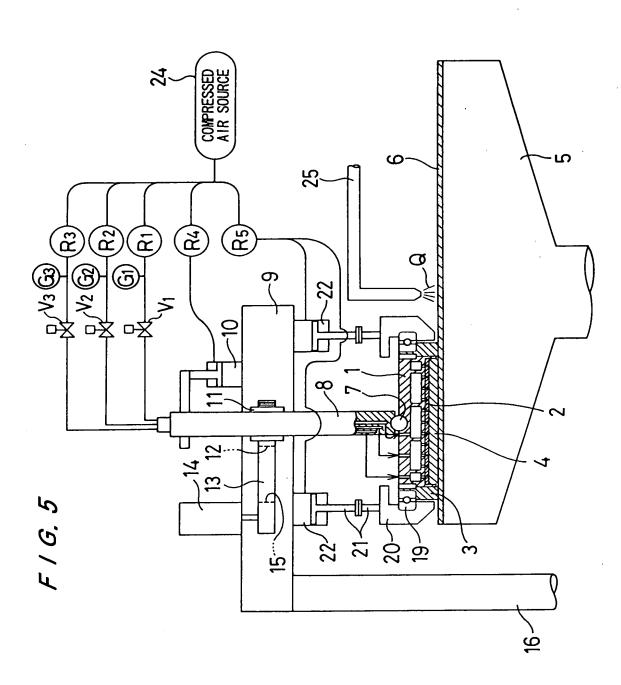
3/8 2 THE PRESSURIZED FLUID IS SUPPLIED ONLY TO THE THIRD CHAMBER C3 2 DISTANCE FROM WAFER CENTER (mm) 30 F1G.3C \$ ည 09 02 8 8 THICKNESS OF REMOVED MATERIAL (Å) PRESSURE OF PRESSURIZED FLUID 2009f/cm² 9 THE PRESSURIZED FLUID IS SUPPLIED ONLY TO THE FIRST CHAMBER C1 20 POLISHING PRESSURE 400gf/cm² DISTANCE FROM WAFER CENTER (mm) ဓ္တ F1G.3B 49 22 09 02 8 8 8 7000 23000 1000 1000 1000 1000 THICKNESS OF REMOVED MATERIAL ($\mbegin{picture}(x) & (\mbegin{picture}(x) & (\mbegin{pict$ 2 29 THE PRESSURIZED FLUID WAS NOT SUPPLIED 30 DISTANCE FROM WAFER CENTER (mm) F16.3A 40 മ 9 2 8 8 23000 23000 2000 2000 2000 2000 WHICKNESS OF REMOVED

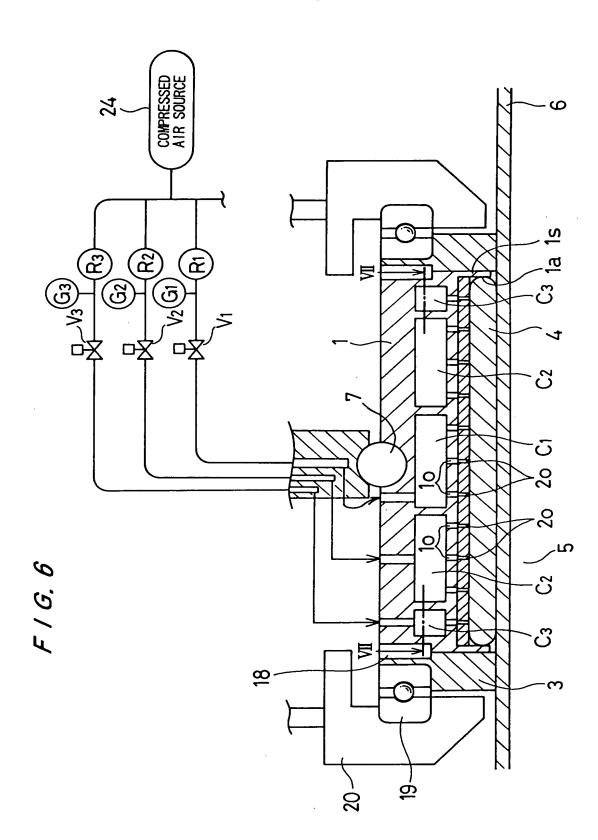
F1G.4E 200 THICKNESS OF REMOVED MATERIAL (Å) F1G.40 DISTANCE FROM WAFER CENTER (mm) 8 8 8 ļδ THICKNESS OF REMOVED MATERIAL (Å) F1G.4C DISTANCE FROM WAFER CENTER (mm) POLISHING PRESSURE:400gf/cm² 6 8 CANCELLED ไร THICKNESS OF REMOVED MATERIAL (Å) 8 F1G.4B DISTANCE FROM WAFER CENTER (mm) 20 THICKNESS OF REMOVED MATERIAL (Å) 8 DISTANCE FROM WAFER CENTER (mm) F1G.4A 000 THICKNESS OF REMOVED MATERIAL (Å)

APPROVED. O.G. FIG.
- BY CLASS SUBCLASS

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Daanywes "Caeca





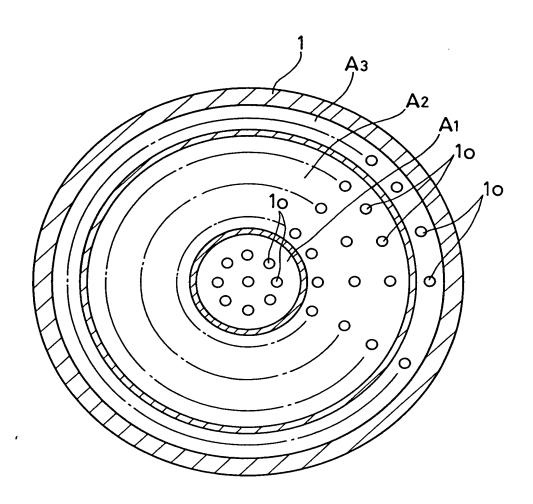
APPROVED O.G. FJG.

BY CLASS SUBCLASS

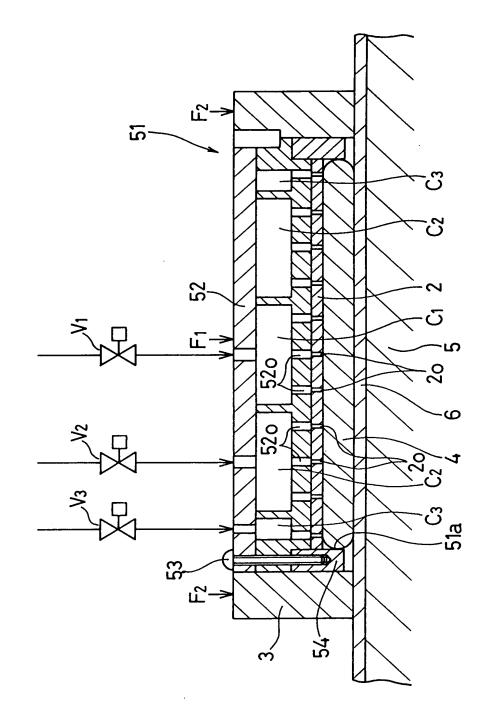
DRAFTSMAH

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F / G. 7



8/8



F1G.8